

1200 V Gen 3 Power SiC Merged PIN Schottky Diode, 1 A



SlimSMA HV (DO-221AC)

Cathode O Anode

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _F	1 A			
V _R	1200 V			
V _F at I _F at 25 °C, typ.	1.35 V			
T _J max.	175 °C			
I _R at V _R at 175 °C	4.5 μΑ			
Q _C (V _R = 800 V)	7.5 nC			
Package	SlimSMA HV (DO-221AC)			
Circuit configuration	Single			

FEATURES

 Minimum creepage distance 3.2 mm guaranteed by design



FREE

Comparative Tracking Index: CTI ≥ 600

- High CTI molding compound provides excellent HALOGEN electrical insulation at relevant working voltages
- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- · Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- · MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 1200 V Schottky diode, designed for high performance and ruggedness.

Optimized for extreme high-speed hard switching over a wide temperature range. It is suited for demanding applications, such as bootstrap and anti-parallel diodes in AC/DC and DC/DC converters.

MECHANICAL DATA

Case: SlimSMA HV (DO-221AC)

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		1200	V	
Continuous forward current	I _F	T _M = 150 °C (DC) ⁽¹⁾	1	Α	
DC blocking voltage	V_{DC}		1200	V	
Repetitive peak forward current	I _{FRM}	T_M = 25 °C, f = 50 Hz, square wave, DC = 25 %	4.9		
Non-repetitive peak forward surge current	I _{FSM}	$T_M = 25$ °C, $t_p = 10$ ms, half sine wave	12.5	Α	
		$T_M = 110$ °C, $t_p = 10$ ms, half sine wave	10.5		
	P _{tot} (1)	$T_{M} = 25 ^{\circ}C$	12.5	w	
Dower dissipation	Ptot ('')	T _M = 110 °C	5.4	7 VV	
Power dissipation P	P _{tot} (2)	$T_{M} = 25 ^{\circ}C$	9.7	w	
	P _{tot} (=)	T _M = 110 °C	4.2] VV	
124	∫i ² dt	T _M = 25 °C	0.8		
I ² t value		T _M = 110 °C	0.6	A ² s	
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C	

Notes

- (1) Based on typical R_{th}
- (2) Based on maximum Rth
- (3) The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta,JA}$



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
		I _F = 1 A	-	1.35	1.50	
Forward voltage	V_{F}	I _F = 1 A, T _J = 150 °C	-	1.73	2.00	V
		I _F = 1 A, T _J = 175 °C	-	1.85	-	
		$V_R = V_R$ rated	-	0.12	10	
Reverse leakage current	I_{R}	V _R = V _R rated, T _J = 150 °C	-	0.70	20	μΑ
		V _R = V _R rated, T _J = 175 °C	-	4.5	-	
Total capacitance C	0	V _R = 1 V, f = 1 MHz	-	67	-	pF
		V _R = 800 V, f = 1 MHz	-	6.0	-	PF
Total capacitive charge	Q_{C}	V _R = 800 V, f = 1 MHz	-	7.5	-	nC

THERMAL AND MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to mount	R _{thJM} ⁽¹⁾		-	12	15.5	°C/W
Marking device				C1	12	

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

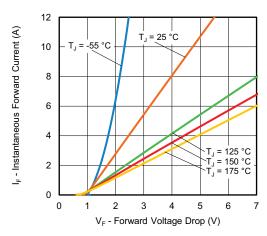


Fig. 1 - Typical Forward Voltage Drop Characteristics

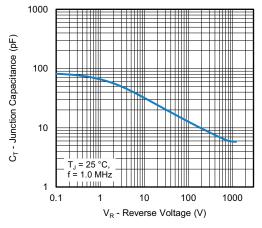


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

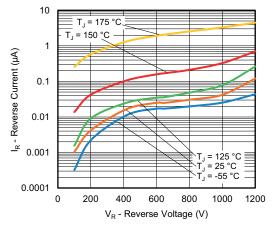


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

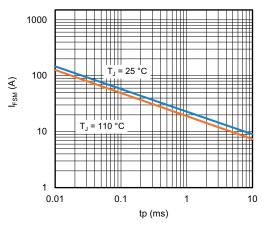


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

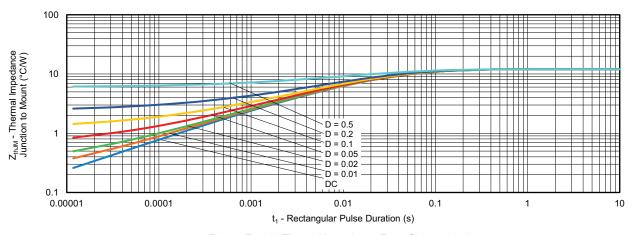


Fig. 5 - Typical Thermal Impedance Z_{thJM} Characteristics

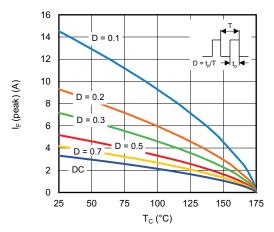


Fig. 6 - Peak Forward Current vs. Maximum Allowable Mount Temperature

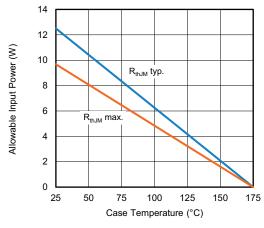


Fig. 7 - Forward Power Loss Characteristics

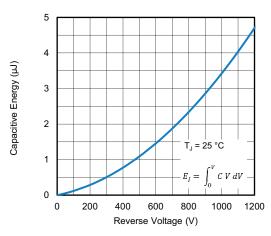


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

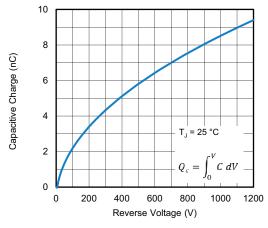
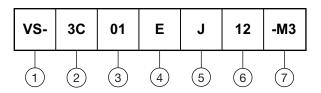


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

- 3C = SiC diode, generation 3

Current rating (01 = 1 A)

4 - E = single diode

J = SlimSMA HV package

6 - Voltage rating: (12 = 1200 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

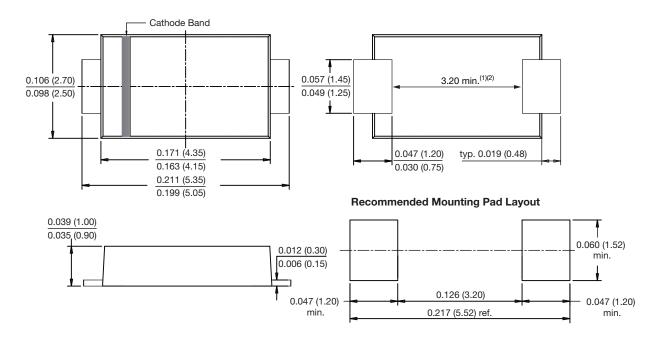
ORDERING INFORMATION					
PREFERRED P/N	UNIT WEIGHT (g)	BASE QUANTITY	PACKAGING DESCRIPTION		
VS-3C01EJ12-M3/H	0.032	3500 per reel	7" diameter plastic tape and reel		
VS-3C01EJ12-M3/I	0.032	14 000 per reel	13" diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?97278		
Part marking information	www.vishay.com/doc?98699		
Packaging information	www.vishay.com/doc?98714		



SlimSMA HV (DO-221AC)

DIMENSIONS in inches (millimeters)



Notes

- (1) Minimum creepage distance is defined and guaranteed by design
- (2) For high voltage applications, end users should consider the relevant guidelines and normative on creepage and clearance distances between device terminals and PCB pads.



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.